Tool ID: 207
Tool Location: 107

Equipment Information Sheet

Plasma-Therm Deep Silicon Etcher

Manager: Jeremy Clark 607-254-6487
Backup: Tom Pennell 607-254-4309

Calls to staff phones will be automatically forwarded to their cell phones during accessible hours. At other times leave a message or send them an email.

SAFETY

- No unusual hazards under normal use
- User must remain in the lab while plasma processing.

USAGE RESTRICTIONS

- No metals allowed in chamber
- Other than standard photoresist, no polymers or adhesives

SCHEDULING/SIGN-UP RESTRICTIONS

Minimum Tool Time: 30 minutes

MATERIALS COMPATIBILITY CATEGORY

Tool Category 2: Silicon Based Substrates and Select Refractory Metals

Allowed	Not Allowed
Tool category 1/1E materials	No Glass Substrates
Silicon Based Materials only	No CNF Class A or Class B metals and oxides/compounds of (exposed or buried) (ie Magnesium, Zinc, Barium, Calcium)
Si, SiC, SiO_2 substrates	
All Furnace grown or deposited films	
PECVD Films	No Gold, Silver or Copper (Exposed or buried)
ALD dieletric films	No High Vapor pressure materials
CNF Refractory Metals (ie Al, Ti,Ta,W,Pt,Mo,Cr,Ni)	No III/V Compound Semiconductors
Nitrides and Oxides of above metals	No Organic/Biology Molecules prepared-with or without Salt buffers
Cured organics and baked Photoresist	

High Vapor Pressure Metals and Compounds are materials that have a vapor pressure above 1e-6 Torr at 400 C.

Additional Material Restrictions and Exceptions

- Whole 4 wafers only
- Thermal / PECVD SiO2, photoresist, Al2O3 etch masks ONLY
- If mask is resist, 5mm of the edge must be removed
- See tool manager about bonding wafer pieces to carrier

Last Updated: 04/08/2026